

Title (en)
FERROELECTRIC MEMORY DEVICE

Title (de)
FERROELEKTRISCHE SPEICHERVORRICHTUNG

Title (fr)
DISPOSITIF DE MEMOIRE FERROELECTRIQUE

Publication
EP 2987178 A1 20160224 (FR)

Application
EP 14725226 A 20140416

Priority
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Abstract (en)
[origin: WO2014170606A1] The invention relates to a ferroelectric memory device comprising at least one layer comprising a ferroelectric polymer, and at least two electrodes either side thereof, the ferroelectric polymer being of general formula P(VDF-X-Y), wherein VDF is vinylidene fluoride motifs, X is trifluoroethylene or tetrafluoroethylene motifs, and Y is motifs from a third monomer, the molar proportion of Y motifs in the polymer being less than or equal to 6.5%.

IPC 8 full level
H01L 21/28 (2006.01); **C08F 214/18** (2006.01); **G11C 11/22** (2006.01); **H01G 4/14** (2006.01); **H01L 21/336** (2006.01); **H01L 27/10** (2006.01); **H01L 27/28** (2006.01); **H01L 29/51** (2006.01); **H01L 29/66** (2006.01); **H01L 29/78** (2006.01); **H01L 29/861** (2006.01); **H01L 49/02** (2006.01); **H01L 51/00** (2006.01); **H01L 51/05** (2006.01)

CPC (source: EP US)
C08F 214/22 (2013.01 - EP US); **H01G 4/14** (2013.01 - EP US); **H01G 4/18** (2013.01 - EP US); **H01G 4/33** (2013.01 - EP US); **H01G 7/06** (2013.01 - EP US); **H01L 27/101** (2013.01 - US); **H01L 28/40** (2013.01 - EP US); **H01L 29/40111** (2019.08 - EP US); **H01L 29/516** (2013.01 - EP US); **H01L 29/6684** (2013.01 - EP US); **H01L 29/78391** (2014.09 - EP US); **H01L 29/861** (2013.01 - EP US); **H10B 51/30** (2023.02 - US); **H10B 53/30** (2023.02 - US); **H10K 10/20** (2023.02 - EP US); **H10K 19/202** (2023.02 - US); **H10K 85/10** (2023.02 - EP US); **H10K 85/151** (2023.02 - EP US); **H01L 28/55** (2013.01 - EP US); **H10B 51/00** (2023.02 - EP US); **H10B 53/00** (2023.02 - EP US); **H10K 19/202** (2023.02 - EP); **H10K 85/141** (2023.02 - US)

C-Set (source: EP US)
1. **C08F 214/22 + C08F 214/26**
2. **C08F 214/22 + C08F 214/18**

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
WO 2014170606 A1 20141023; CN 105283945 A 20160127; CN 105283945 B 20191008; EP 2987178 A1 20160224; FR 3004854 A1 20141024; FR 3004854 B1 20150417; JP 2016522569 A 20160728; KR 20150145257 A 20151229; US 10199384 B2 20190205; US 2016071852 A1 20160310

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